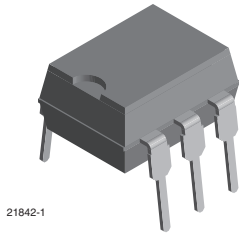
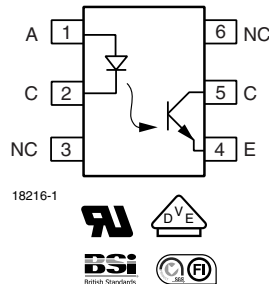


Optocoupler, Phototransistor Output, no Base Connection



21842-1



18216-1



FEATURES

- Isolation test voltage, 5300 V_{RMS}
- No base terminal connection for improved common mode interface immunity
- Long term stability
- Industry standard dual-in-line package
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC


RoHS
COMPLIANT

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-2 (VDE 0884) available with option 1
- BSI IEC 60950; IEC 60065
- FIMKO

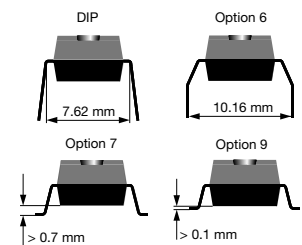
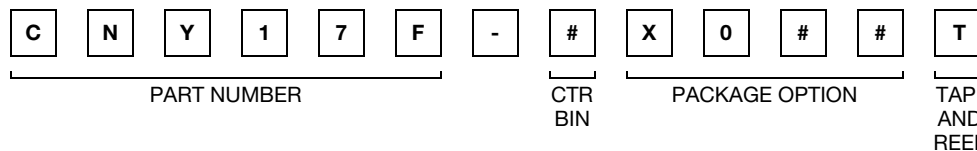
DESCRIPTION

The CNY17F is an optocoupler consisting of a gallium arsenide infrared emitting diode optically coupled to a silicon planar phototransistor detector in a plastic plug-in DIP-6 package.

The coupling device is suitable for signal transmission between two electrically separated circuits. The potential difference between the circuits to be coupled is not allowed to exceed the maximum permissible reference voltages.

In contrast to the CNY17 series, the base terminal of the F type is not connected, resulting in a substantially improved common-mode interference immunity.

ORDERING INFORMATION



AGENCY CERTIFIED/PACKAGE	CTR (%)			
	40 to 80	63 to 125	100 to 200	160 to 320
UL, BSI, FIMKO				
DIP-6	CNY17F-1	CNY17F-2	CNY17F-3	CNY17F-4
DIP-6, 400 mil, option 6	CNY17F-1X006	CNY17F-2X006	CNY17F-3X006	CNY17F-4X006
SMD-6, option 7	CNY17F-1X007 ⁽¹⁾	CNY17F-2X007T ⁽¹⁾	CNY17F-3X007T ⁽¹⁾	CNY17F-4X007T ⁽¹⁾
SMD-6, option 9	CNY17F-1X009T ⁽¹⁾	CNY17F-2X009T ⁽¹⁾	CNY17F-3X009T ⁽¹⁾	CNY17F-4X009T ⁽¹⁾
VDE, UL, BSI, FIMKO				
DIP-6	CNY17F-1X001	CNY17F-2X001	CNY17F-3X001	CNY17F-4X001
DIP-6, 400 mil, option 6	CNY17F-1X016	CNY17F-2X016	CNY17F-3X016	CNY17F-4X016
SMD-6, option 7	CNY17F-1X017 ⁽¹⁾	CNY17F-2X017 ⁽¹⁾	CNY17F-3X017 ⁽¹⁾	CNY17F-4X017 ⁽¹⁾
SMD-6, option 9	CNY17F-1X019	CNY17F-2X019 ⁽¹⁾	CNY17F-3X019 ⁽¹⁾	-

Note

⁽¹⁾ Also available in tubes; do not put T on end.

Vishay Semiconductors Optocoupler, Phototransistor Output, no Base Connection

ABSOLUTE MAXIMUM RATINGS (1) ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
DC forward current		I_F	60	mA
Surge forward current	$t \leq 10\text{ }\mu\text{s}$	I_{FSM}	2.5	A
Power dissipation		P_{diss}	100	mW
OUTPUT				
Collector emitter breakdown voltage		BV_{CEO}	70	V
Collector current		I_C	50	mA
	$t \leq 1\text{ ms}$	I_C	100	mA
Total power dissipation		P_{diss}	150	mW
COUPLER				
Isolation test voltage between emitter and detector		V_{ISO}	5300	V_{RMS}
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Isolation thickness between emitter and detector			≥ 0.4	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1			175	
Isolation resistance	$V_{IO} = 500\text{ V}$	R_{IO}	$\geq 10^{11}$	Ω
Storage temperature range		T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Ambient temperature range		T_{amb}	- 55 to + 100	$^{\circ}\text{C}$
Junction temperature		T_J	100	$^{\circ}\text{C}$
Soldering temperature (2)	max. 10 s, dip soldering: distance to seating plane $\geq 1.5\text{ mm}$	T_{sld}	260	$^{\circ}\text{C}$

Note

(1) Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to reflow profile for soldering conditions for surface mounted parts (SMD). Refer to wave profile for soldering conditions for through hole parts (DIP).

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	$I_F = 60\text{ mA}$		V_F		1.25	1.65	V
Breakdown voltage	$I_R = 10\text{ }\mu\text{A}$		V_{BR}	6			V
Reverse current	$V_R = 6\text{ V}$		I_R		0.01	10	μA
Capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$		C_O		25		pF
Thermal resistance			R_{th}		750		K/W
OUTPUT							
Collector emitter capacitance	$V_{CE} = 5\text{ V}$, $f = 1\text{ MHz}$		C_{CE}		5.2		pF
Base collector capacitance	$V_{CE} = 5\text{ V}$, $f = 1\text{ MHz}$		C_{BC}		6.5		pF
Emitter base capacitance	$V_{CE} = 5\text{ V}$, $f = 1\text{ MHz}$		C_{EB}		7.5		pF
Thermal resistance			R_{th}		500		K/W
COUPLER							
Collector emitter, saturation voltage	$I_F = 10\text{ mA}$, $I_C = 2.5\text{ mA}$		V_{CEsat}		0.25	0.4	V
Coupling capacitance			C_C		0.6		pF
Collector emitter, leakage current	$V_{CE} = 10\text{ V}$	CNY17F-1	I_{CEO}		2	50	nA
		CNY17F-2	I_{CEO}		2	50	nA
		CNY17F-3	I_{CEO}		5	100	nA
		CNY17F-4	I_{CEO}		5	100	nA

Note

- Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

Optocoupler, Phototransistor Output, Vishay Semiconductors
no Base Connection

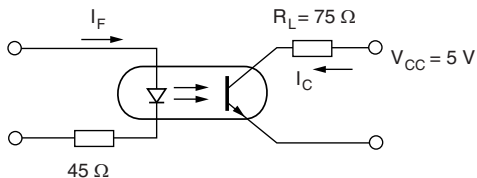
CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$I_F = 10 \text{ mA}$	CNY17F-1	CTR	40		80	%
		CNY17F-2	CTR	63		125	%
		CNY17F-3	CTR	100		200	%
		CNY17F-4	CTR	160		320	%
	$I_F = 1 \text{ mA}$	CNY17F-1	CTR	13	30		%
		CNY17F-2	CTR	22	45		%
		CNY17F-3	CTR	34	70		%
		CNY17F-4	CTR	56	90		%

Note

- Current transfer ratio I_C/I_F at $V_{CE} = 5 \text{ V}$, $25 \text{ }^\circ\text{C}$ and collector emitter leakage current by dash number.

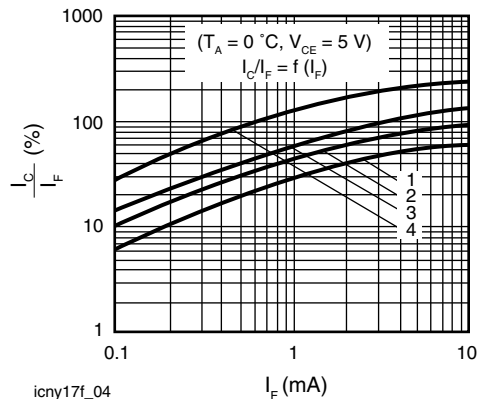
SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
LINEAR OPERATION (without saturation)							
Turn-on time	$I_F = 10 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 75 \text{ } \Omega$		t_{on}		3		μs
Rise time	$I_F = 10 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 75 \text{ } \Omega$		t_r		2		μs
Turn-off time	$I_F = 10 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 75 \text{ } \Omega$		t_{off}		2.3		μs
Fall time	$I_F = 10 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 75 \text{ } \Omega$		t_f		2		μs
Cut-off frequency	$I_F = 10 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 75 \text{ } \Omega$		f_{CO}		250		kHz
SWITCHING OPERATION (with saturation)							
Turn-on time	$I_F = 20 \text{ mA}$	CNY17F-1	t_{on}		3		μs
	$I_F = 10 \text{ mA}$	CNY17F-2	t_{on}		4.2		μs
		CNY17F-3	t_{on}		4.2		μs
		CNY17F-4	t_{on}		6		μs
Rise time	$I_F = 20 \text{ mA}$	CNY17F-1	t_r		2		μs
	$I_F = 10 \text{ mA}$	CNY17F-2	t_r		3		μs
		CNY17F-3	t_r		3		μs
	$I_F = 5 \text{ mA}$	CNY17F-4	t_r		4.6		μs
Turn-off time	$I_F = 20 \text{ mA}$	CNY17F-1	t_{off}		18		μs
	$I_F = 10 \text{ mA}$	CNY17F-2	t_{off}		23		μs
		CNY17F-3	t_{off}		23		μs
		CNY17F-4	t_{off}		25		μs
Fall time	$I_F = 20 \text{ mA}$	CNY17F-1	t_f		11		μs
	$I_F = 10 \text{ mA}$	CNY17F-2	t_f		14		μs
		CNY17F-3	t_f		14		μs
	$I_F = 5 \text{ mA}$	CNY17F-4	t_f		15		μs

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)



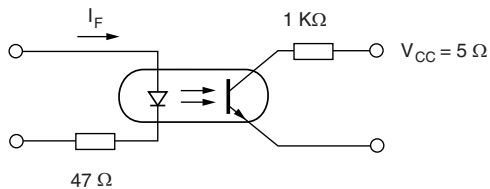
icny17f_01

Fig. 1 - Linear Operation (without Saturation)



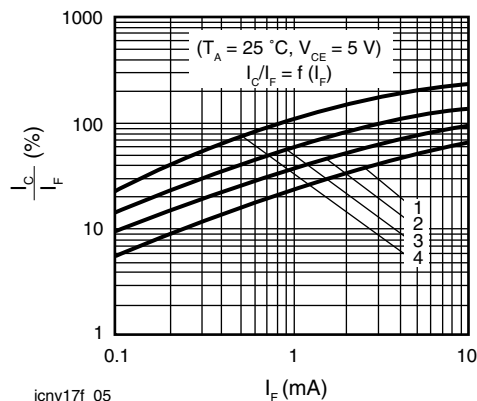
icny17f_04

Fig. 4 - Current Transfer Ratio vs. Diode Current



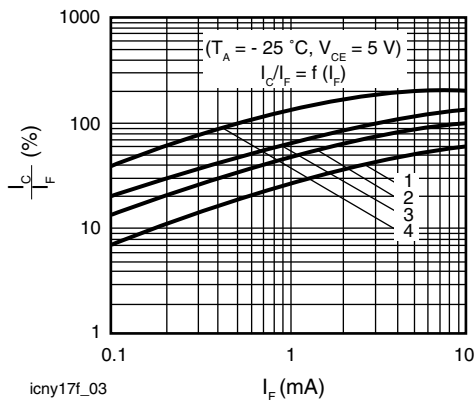
icny17f_02

Fig. 2 - Switching Operation (with Saturation)



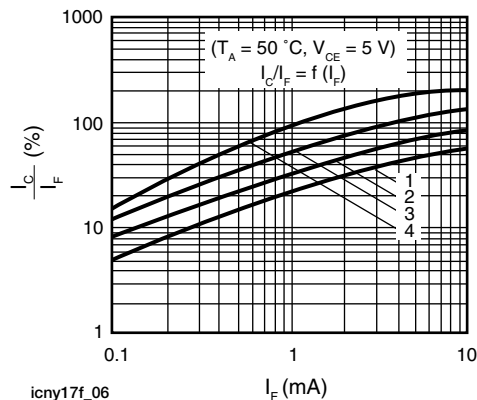
icny17f_05

Fig. 5 - Current Transfer Ratio vs. Diode Current



icny17f_03

Fig. 3 - Current Transfer Ratio vs. Diode Current



icny17f_06

Fig. 6 - Current Transfer Ratio vs. Diode Current

Optocoupler, Phototransistor Output, Vishay Semiconductors
no Base Connection

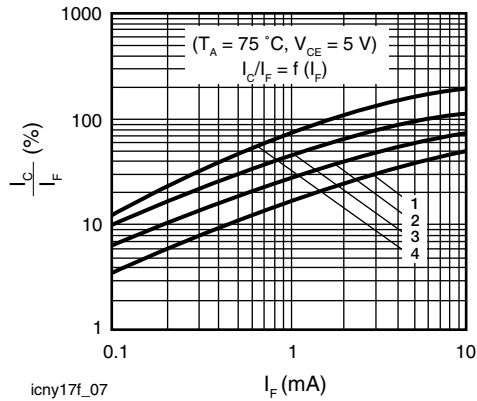


Fig. 7 - Current Transfer Ratio vs. Diode Current

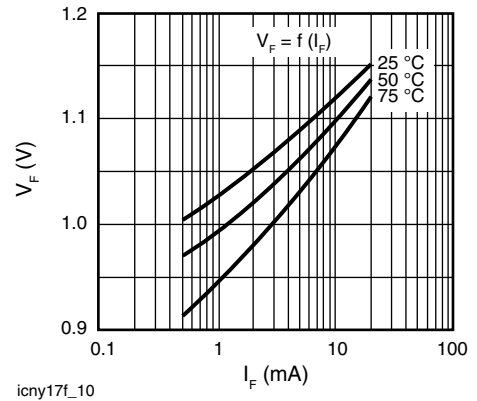


Fig. 10 - Forward Voltage

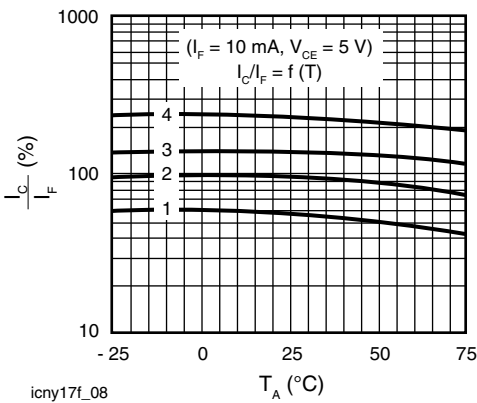


Fig. 8 - Current Transfer Ratio (CTR) vs. Temperature

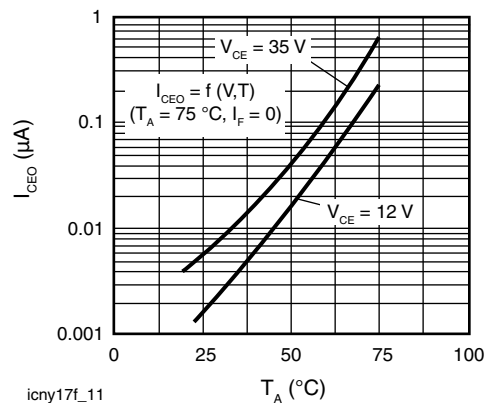


Fig. 11 - Collector Emitter Off-state Current

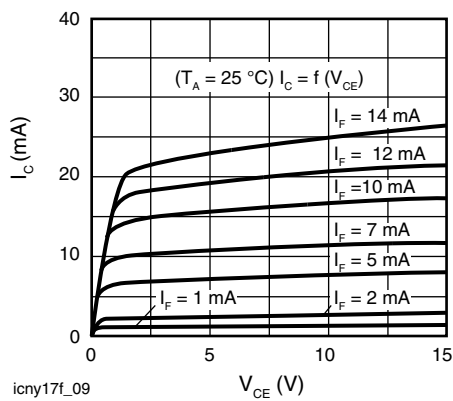


Fig. 9 - Output Characteristics CNY17F-2, -3

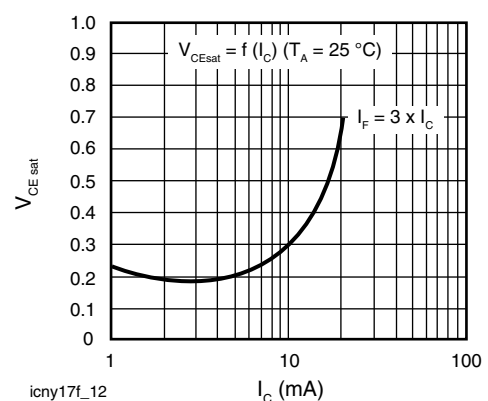


Fig. 12 - Saturation Voltage vs. Collector Current and Modulation Depth CNY17F-1

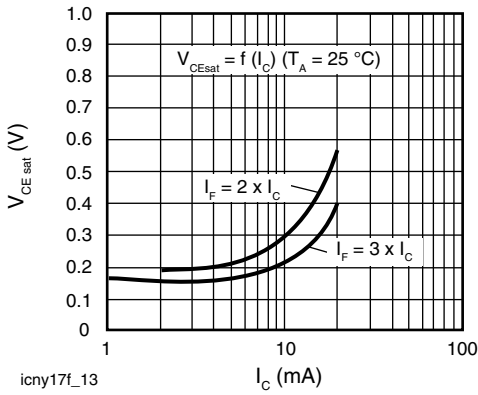


Fig. 13 - Saturation Voltage vs. Collector Current and Modulation Depth CNY17F-2

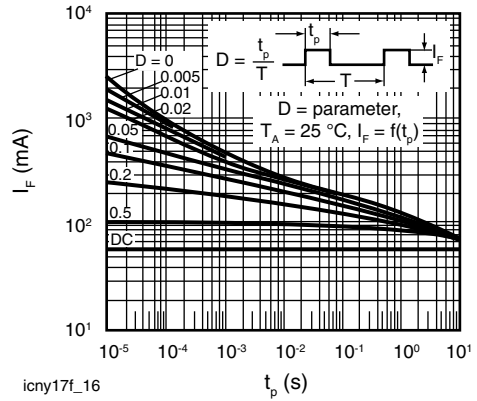


Fig. 16 - Permissible Pulse Load

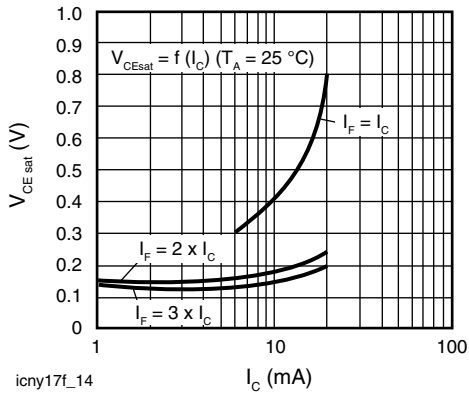


Fig. 14 - Saturation Voltage vs. Collector Current and Modulation Depth CNY17F-3

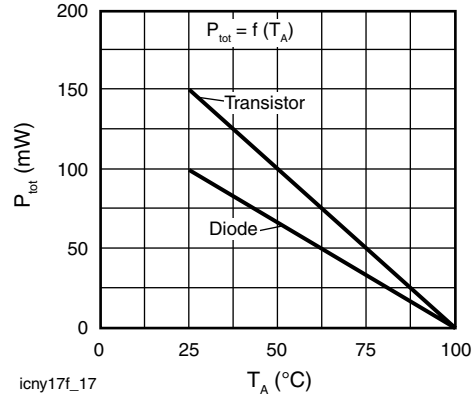


Fig. 17 - Permissible Power Dissipation for Transistor and Diode

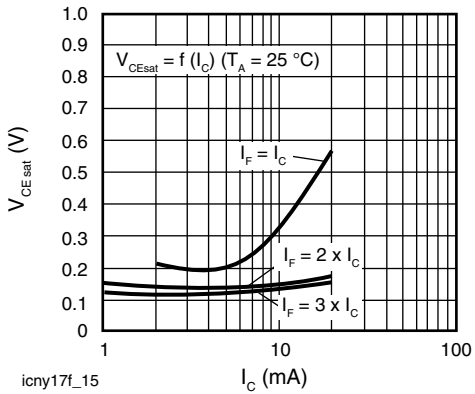


Fig. 15 - Saturation Voltage vs. Collector Current and Modulation Depth CNY17F-4

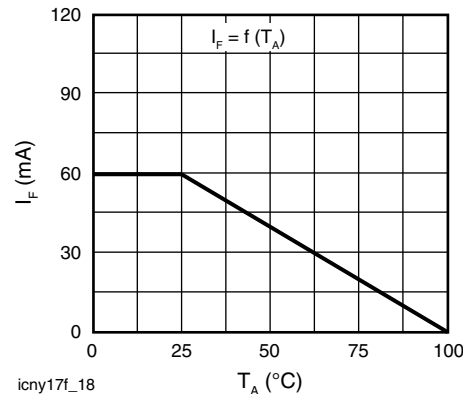


Fig. 18 - Permissible Forward Current Diode

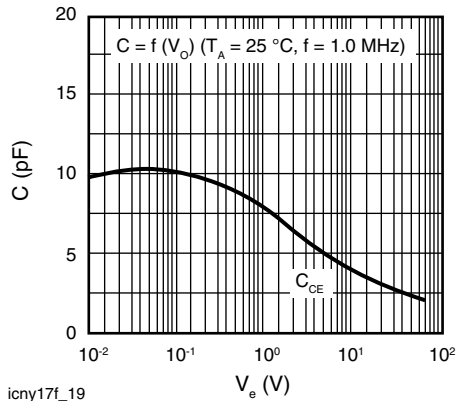
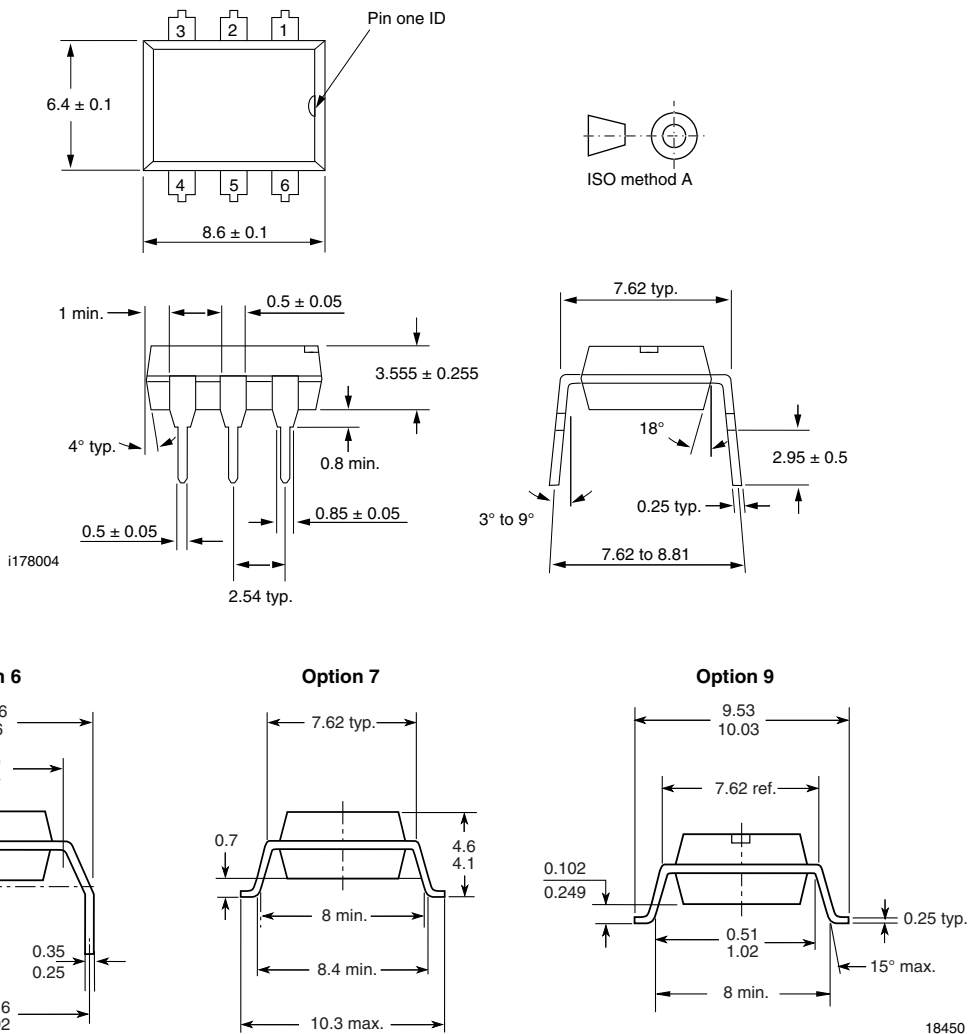


Fig. 19 - Transistor Capacitance

PACKAGE DIMENSIONS in millimeters




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